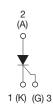


VS-16TTS...PbF Series, VS-16TTS...-M3 Series

Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 16 A



TO-220AB

PRODUCT SUMMARY					
Package TO-220AB					
Diode variation	Single SCR				
I _{T(AV)}	10 A				
V _{DRM} /V _{RRM}	800 V, 1200 V				
V _{TM}	1.4 V				
I _{GT}	60 mA				
T_J	- 40 °C to 125 °C				

FEATURES

- Designed and qualified according JEDEC-JESD47
- 125 °C max. operating junction temperature
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912







APPLICATIONS

· Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery

DESCRIPTION

The VS-16TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operating up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS							
Capacitive input filter T _A = 55 °C, T _J = 125 °C, common heatsink of 1 °C/W							

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
I _{T(AV)}	Sinusoidal waveform	10	۸			
I _{RMS}		16	Α			
V _{DRM} /V _{RRM}	Range (1)	800/1200	V			
I _{TSM}		200	A			
V _T	10 A, T _J = 25 °C	1.4	V			
dV/dt		500	V/µs			
dl/dt		150	A/μs			
T _J	Range	- 40 to 125	°C			

Note

⁽¹⁾ For higher voltage up to 1600 V contact factory

VOLTAGE RATINGS								
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA					
VS-16TTS08PbF, VS-16TTS08-M3	800	800	10					
VS-16TTS12PbF, VS-16TTS12-M3	1200	1200	- 10					



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ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES		UNITS	
PARAMETER	STIVIBUL		TEST CONDITIONS	TYP.	MAX.	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 98 °C, 1	80° conduction, half sine wave	1	0		
Maximum RMS on-state current	I _{RMS}			1	6	Α	
Maximum peak, one-cycle,	I	10 ms sine p	ulse, rated V _{RRM} applied	17	70	_ ^	
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied	20	00		
Maximum I ² t for fusing	I ² t	10 ms sine p	ulse, rated V _{RRM} applied	14	14	A ² s	
Waximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied		200		A-S	
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 r	t = 0.1 to 10 ms, no voltage reapplied		00	A²√s	
Maximum on-state voltage drop	V_{TM}	10 A, T _J = 25 °C		1.4		V	
On-state slope resistance	r _t	T 405.00		T ₁ = 125 °C		.0	mΩ
Threshold voltage	V _{T(TO)}	1.1		.1	V		
Maximum reverse and direct leakage current	1 /1	T _J = 25 °C	V - Botod V A	0	.5		
waximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	J = 125 °C V _R = Rated V _{RRM} /V _{DRM}		0		
Holding current	l _Η	Anode supply = 6 V, resistive load, initial I _T = 1 A 16TTS08PbF, 16TTS12PbF, T _J = 25 °C		-	150	mA	
Maximum latching current	Ι _L	Anode supply = 6 V, resistive load, T _J = 25 °C		Anode supply = 6 V, resistive load, T _J = 25 °C 200		00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J \text{ max., linear to } 80 ^{\circ}\text{C, } V_{DRM} = R_g - k = Open$		50	00	V/µs	
Maximum rate of rise of turned-on current	dI/dt			15	50	A/µs	

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P_{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	VV		
Maximum peak positive gate current	+ I _{GM}		1.5	Α		
Maximum peak negative gate voltage	- V _{GM}		10	V		
	I _{GT}	Anode supply = 6 V, resistive load, T _J = - 65 °C	90	mA		
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T _J = 25 °C	60			
		Anode supply = 6 V, resistive load, T _J = 125 °C	35			
		Anode supply = 6 V, resistive load, T _J = - 65 °C	3.0			
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	v		
voltage to trigger		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V		
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C V = Poted value	0.25			
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA		

SWITCHING							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9				
Typical reverse recovery time	t _{rr}	T. – 105 °C	4	μs			
Typical turn-off time	tq	T _J = 125 °C	110				

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum junction and storage temperature range		T _J , T _{Stg}		- 40 to 125	°C	
Maximum thermal resistance, junction to case		R_{thJC}	DC operation	1.3		
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W	
Typical thermal resistance, case to heatsink		R_{thCS}	Mounting surface, smooth and greased	0.5		
Approximate weight				2	g	
Approximate weight				0.07	OZ.	
Mounting torque ———	minimum			6 (5)	kgf · cm	
	maximum			12 (10)	(lbf · in)	
			Coop obula TO 200AB	16T7	ΓS08	
Marking device			Case style TO-220AB		16TTS12	

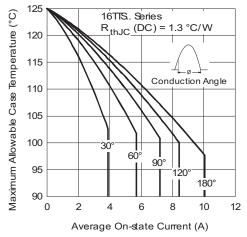


Fig. 1 - Current Rating Characteristics

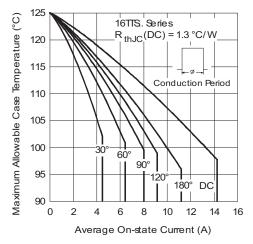


Fig. 2 - Current Rating Characteristics

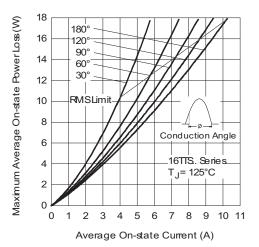


Fig. 3 - On-State Power Loss Characteristics

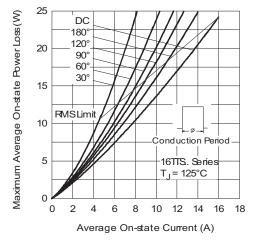


Fig. 4 - On-State Power Loss Characteristics

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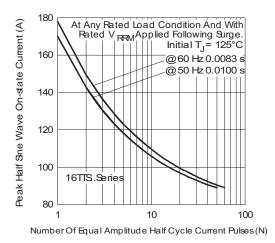


Fig. 5 - Maximum Non-Repetitive Surge Current

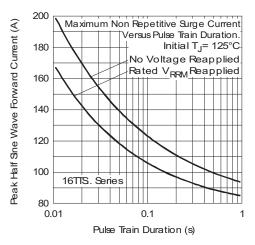


Fig. 6 - Maximum Non-Repetitive Surge Current

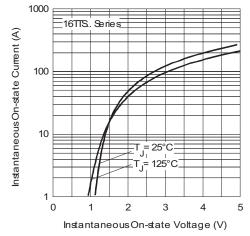


Fig. 7 - On-State Voltage Drop Characteristics

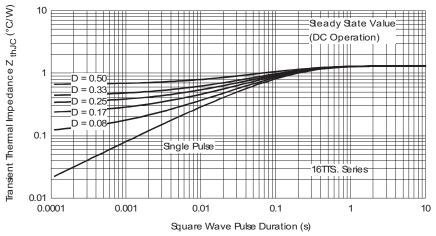


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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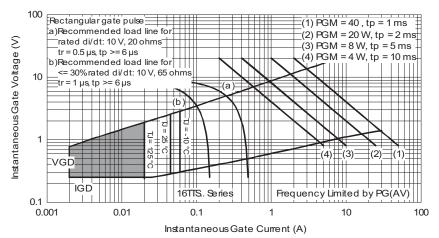
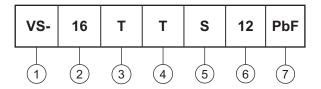


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating

3 - Circuit configuration:

T = Single thyristor

4 - Package:

T = TO-220AB

5 - Type of silicon:

S = Converter grade

6 - Voltage code x 100 = V_{RRM} - 08 = 800 V 12 = 1200 V

7 | - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-16TTS08PbF	50	1000	Antistatic plastic tubes					
VS-16TTS08-M3	50	1000	Antistatic plastic tubes					
VS-16TTS12PbF	50	1000	Antistatic plastic tubes					
VS-16TTS12-M3	50	1000	Antistatic plastic tubes					

LINKS TO RELATED DOCUMENTS							
Dimensions www.vishay.com/doc?95222							
Dark mandring information	TO-220AB PbF	www.vishay.com/doc?95225					
Part marking information	TO-220AB -M3	www.vishay.com/doc?95028					



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOIES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		
		•	•	•	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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